

Application No.: 10/771,566

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Docket No.: 245402008300

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (currently amended): An electrode employing a nitride-based semiconductor of III-V group compound, comprising:

a nitride-based semiconductor layer of III-V group compound;

an electrode metal;

a metal oxide inserted between said nitride-based semiconductor layer of III-V group compound and said electrode metal; and

a nitride semiconductor intermediate layer doped with oxygen, said nitride semiconductor intermediate layer formed during a heating process from said metal oxide and said nitride-based semiconductor layer of III-V group compound between said electrode metal and the underlying nitride based semiconductor layer of III-V group compound[.], wherein the metal of said metal oxide includes at least one of lanthanum (La), cerium (Ce), praseodymium (Pr), neodymium (Nd), promethium (Pm), samarium (Sm), europium (Eu), gadolinium (Gd), terbium (Tb), dysprosium (Dy), holmium (Ho), erbium (Er), thulium (Tm), ytterbium (Yb), and lutetium (Lu).

Claims 2-4 (cancelled)

Claim 5 (withdrawn): A producing method of an electrode employing a nitride-based semiconductor of III-V group compound, comprising the steps of:

forming a nitride-based semiconductor layer of III-V group compound;

forming an electrode metal; and

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inserting a metal oxide between said nitride-based semiconductor layer of III-V group compound and said electrode metal in an oxygen-deficient state.

Claim 6 (withdrawn): The producing method of an electrode employing a nitride-based semiconductor of III-V group compound according to claim 5, wherein said step of inserting the metal oxide is conducted by sputtering or evaporation.

Claim 7 (new): A nitride-based semiconductor device of III-V group compound comprising the electrode according to claim 1.

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